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ITS3 TDR

ALICE collaboration

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Contents

1 Executive Summary	7
2 Introduction	9
2.1 Summary of Physics objectives - Motivation and goals - ITS2 limitations	9
2.2 Summary of detector description and specification - Detector layout, beam conditions	11
2.3 Summary of R&D and production plan	12
2.4 Description of document	12
3 Sensor ASIC	13
3.1 Specifications and challenges (adding to specifications from introduction)	13
3.2 Sensor principle and implementation	13
3.3 Stitching principle and implementation	13
3.4 Readout principle and implementation	13
3.5 Power distribution	13
3.6 Technology & Developments	13
3.6.1 Process optimization	14
3.6.2 DPTS	16
3.6.3 APTS	17
3.6.4 CE65	19
3.6.5 Transistor test structures	19
3.6.6 Building blocks	22
3.6.7 MOSS	23
3.6.8 MOST	23
3.7 Qualification	24
3.7.1 Introduction to qualification strategy	24
3.7.2 Process modification selection	24
3.7.3 Process split selection	24
3.7.4 Reverse bias	25
3.7.5 Radiation hardness	27
3.7.6 Detection efficiency and fake-hit rate	28
3.7.7 Spatial resolution and cluster size	29
3.7.8 Power consumption?	29
3.7.9 Stitched sensor testing: TBD later	31
3.8 Summary of results and development plan	31
4 Detector components and integration	33
4.1 Requirements and challenges	33
4.2 Detector layer	34
4.2.1 Material budget	35
4.3 Mechanics and cooling	36
4.3.1 Design	36
4.3.2 Materials and production processes	36
4.3.3 Thermal characterization	42
4.3.4 Mechanical characterisation	44

4.3.5	Mechanics and cooling alternative designs	46
4.4	Flexible printed circuit	50
4.4.1	FPC tails assembly	50
4.4.2	FPC electrical characterization	51
4.5	Detector assembly	54
4.5.1	H-layer assembly	54
4.5.2	Layers test and characterisation	57
4.5.3	H-layers integration	58
4.5.4	H-detector inspection	58
4.5.5	Detector alternative layout	59
4.6	Silicon thinning	60
4.6.1	Single reticle	60
4.6.2	Full wafer	60
4.7	Silicon bending	61
4.7.1	Mechanical properties of bent silicon	61
4.7.2	Bending curvature radius	62
4.8	Interconnections	63
4.8.1	Wire-bonding technique	63
4.8.2	Fall-back options	63
4.9	Bent ALPIDE characterisation	63
4.9.1	Introduction	64
4.9.2	Electrical performance after bending	64
4.9.3	In-beam performance	64
4.9.4	Stretching effects on ALPIDE	65
4.10	65 nm technology assessment	66
4.10.1	65 nm electrical performance after bending	67
4.10.2	Stretching effects on 65 nm	67
4.11	ITS3 large scale prototype: super-ALPIDE	68
4.11.1	Description	68
4.11.2	Assembly	70
4.11.3	Functional characterization	70
5	Global support structure, services and installation	73
5.1	General requirements	73
5.2	Service support structure	73
5.3	Services	74
5.4	Beam pipe	75
5.5	Installation and removal	77
5.5.1	Sequence	78
5.6	Survey and mechanical alignment	78
6	Off-detector electronics	81
6.1	System Summary	81
6.2	Readout, Data transmission from sensor to off-detector electronics	81
6.2.1	Data rates and readout concept	81
6.2.2	Studies and architecture	81
6.2.3	Radiation Environment	81
6.3	Power supply distribution	81
6.4	Detector control, configuration, calibration procedures	81
6.4.1	Configuration time	81

7 Detector performance	85
7.1 Simulation and reconstruction	85
7.1.1 Simulation	85
7.1.2 Reconstruction	86
7.2 Particle density and radiation load	86
7.3 Single-track efficiency and pointing resolution with standard layout	90
7.4 Impact of dead zones	90
7.4.1 Single-track	90
7.4.2 HF decay reconstruction	90
7.5 Performance for beauty-strange mesons	90
7.6 Definition of layout	90
7.6.1 Impact for strangeness tracking	90
7.6.2 Impact for single-track efficiency (matching)	90
7.7 Effect of misalignment	90
8 Milestones	95
9 Resources	97